

Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE      STATEMENT BY APPLICANT</b> <small>(Use as many sheets as necessary)</small>		<i>Complete if Known</i>	
		Application Number	10/081818
		Filing Date	February 20, 2002
		First Named Inventor	Eldridge, Jerome
		Group Art Unit	2818
		Examiner Name	Ho, Tu-Tu
Sheet 1 of 5		Attorney Docket No: 1303.045US1	

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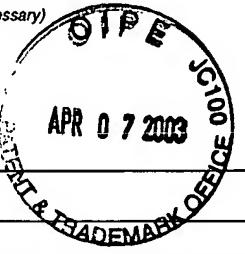
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		<table border="1"> <tr> <td>Application Number</td> <td colspan="4">10/081818</td> </tr> <tr> <td>Filing Date</td> <td colspan="4">February 20, 2002</td> </tr> <tr> <td>First Named Inventor</td> <td colspan="4">Eldridge, Jerome</td> </tr> <tr> <td>Group Art Unit</td> <td colspan="4">2818</td> </tr> <tr> <td>Examiner Name</td> <td colspan="4">Ho, Tu-Tu</td> </tr> </table>					Application Number	10/081818				Filing Date	February 20, 2002				First Named Inventor	Eldridge, Jerome				Group Art Unit	2818				Examiner Name	Ho, Tu-Tu			
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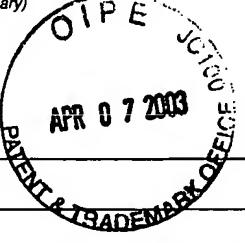
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